

Electronic Supplementary Information for

Enhanced efficiency and high temperature stability of hybrid quantum dot light-emitting diodes using molybdenum oxide doped hole transport layer

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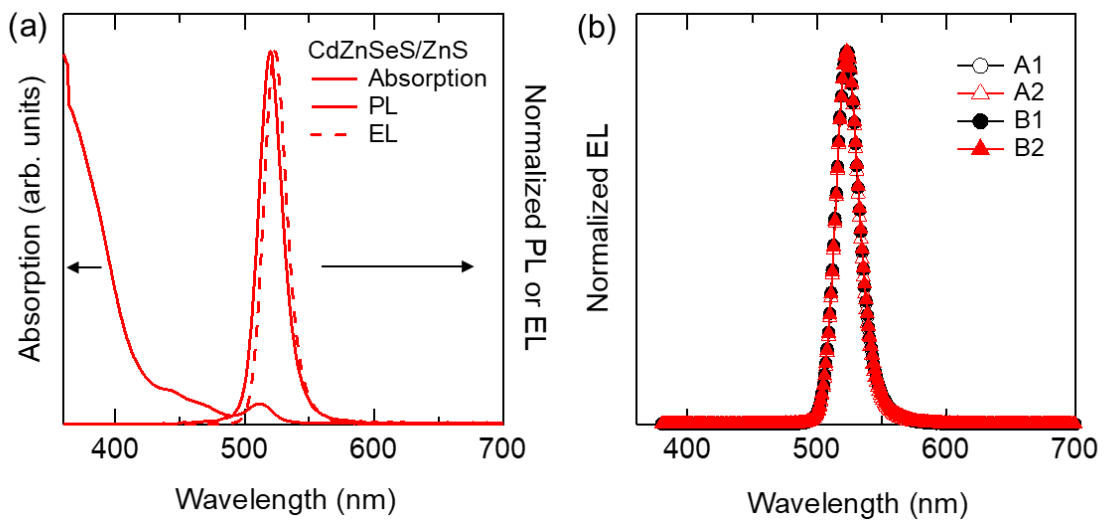


Fig. S1. (a) UV–Vis absorption, PL, and EL spectra of CdZnSeS/ZnS QDs and (b) EL spectrum of the QLEDs.

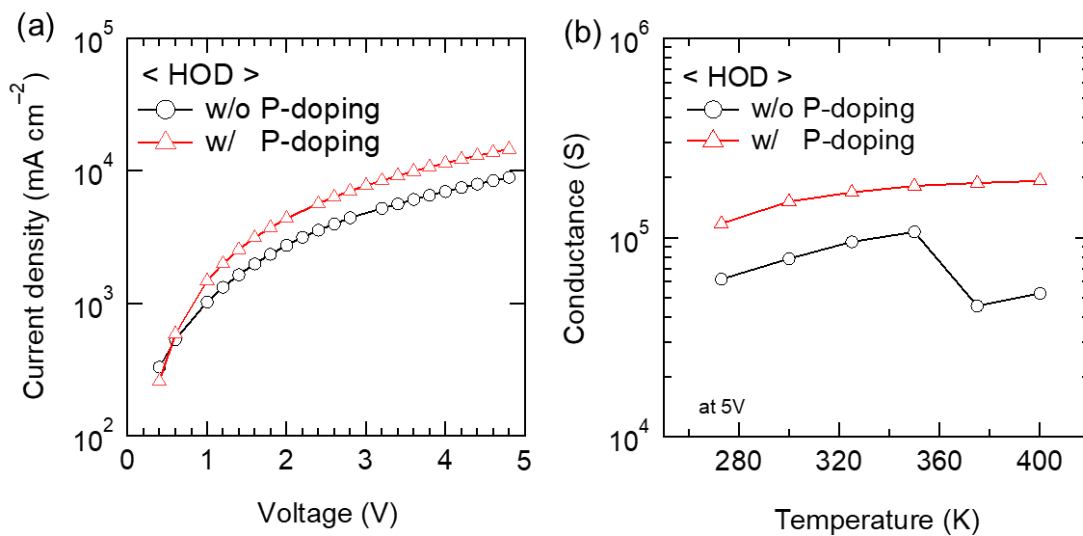


Fig. S2. (a) Current density–voltage characteristics and (b) conductance of the HODs consisting of ITO/MoO₃ (10 nm)/CBP (30 nm)/CBP:MoO₃ (20 nm, 10 vol%) or CBP (20 nm)/MoO₃ (10 nm)/Al (80 nm).

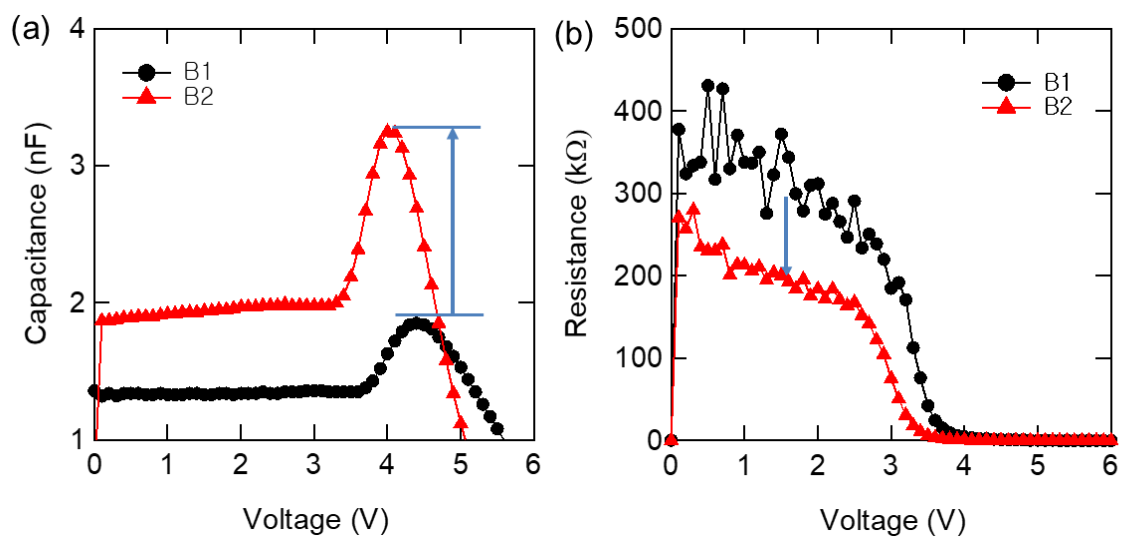


Fig. S3. (a) Capacitance–voltage and (b) resistance–voltage characteristics of Devices **B1** and **B2**.

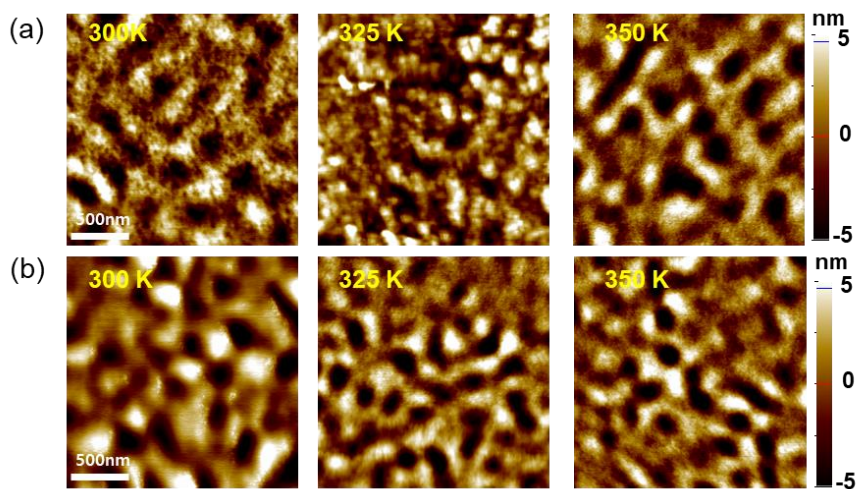


Fig. S4. The surface morphology ($2\ \mu\text{m} \times 2\ \mu\text{m}$) of the (a) CBP (50 nm) and (b) CBP (30 nm)/CBP:MoO₃ (20 nm, 10 vol%) films measured using an AFM at various annealing temperatures from 300 K to 350 K.